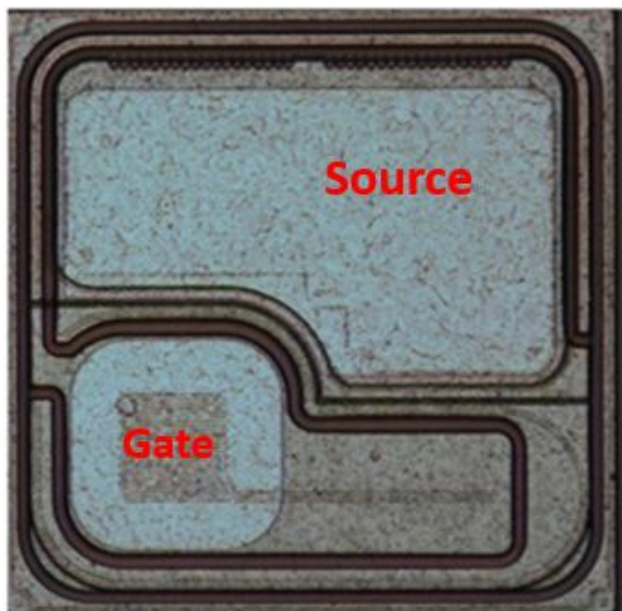


N-channel Enhancement Mode MOSFET With ESD protected



Item	Dimensions	
	um	mil
Die Size (include SL)	310	12.2
Bonding Pad Gate	90*90	3.5*3.5
Bonding Pad Source	98*122	3.9*4.8
Wafer Thickness (D)	152±12	6±0.5
Scribe Line Width (E)	50	1.97
Wafer Size	6"	
Gross Die	161,455	
Top Metal	AlSiCu	
Top Metal Thickness	4um	
Back Metal	Ti/Ni/Ag/Sn	
Back Metal Thickness	1/3/5/14KÅ	

Electrical Characteristics @TA=25°C						
Symbol	Description	Min.	Typ.	Max.	Unit	Test Condition
BV _{DSS}	Drain-Source Breakdown Voltage	61.8			V	V _{GS} =0V · I _D =10uA
V _{GS(th)}	Gate Threshold Voltage	1.1		2.4	V	V _{DS} =V _{GS} · I _D =250uA
R _{DS(ON)}	Drain-Source On –State Resistance			3.6	Ω	V _{GS} =4.5V · I _D =200mA
R _{DS(ON)}	Drain-Source On –State Resistance			2.8	Ω	V _{GS} =10V · I _D =500mA
I _{DSS}	Zero Gate Voltage Drain leakage Current			90	nA	V _{DS} =60V · V _{GS} =0V
I _{GSS}	Gate Body Leakage			±5	uA	V _{GS} =±20V · V _{DS} =0V
V _{FSD}	Source-Drain Diode Forward Voltage			1.2	V	I _S =200mA · V _{GS} =0V

Note:

ESD Protected 2KV For SOT-23 Package.